

ABSTRACT

A metal structure for an integrated circuit, which has copper interconnecting metallization (311) protected by
5 an overcoat layer (320). A portion of the metallization is exposed in a window (301) opened through the thickness of the overcoat layer. The metal structure comprises a patterned conductive barrier layer (330) positioned on the copper metallization, wherein this barrier layer forms a
10 trough with walls (331) conformal with the overcoat window. The height (331a) of the wall is less (between 3 and 20 %) than the overcoat thickness (320a), forming a step (340). A plug (350) of bondable metal, preferably aluminum, is positioned in the trough and has a thickness equal to the
15 trough wall height (331a).